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Appln. No. 10/747,741
Reply to Office Action of August 8, 2007
Amendment dated: February 8, 2008

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AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1 - 15. (Canceled)

16. (Currently Amended) A solid state imaging element, comprising:

~~a pixel, a plurality of pixels arranged in a matrix, each of which has a photoelectric conversion transfer element, a transfer switch for transferring charge stored in said photoelectric conversion transfer element, a charge store part for storing charge transferred by said transfer switch, a reset switch for resetting said charge store part, and an amplifying element for outputting a signal in accordance with a the potential of said charge stored in said charge store part to vertical signal lines;~~

~~wherein said reset switches are comprised of a depletion depression type transistor.~~

17. (Previously Presented) A solid-state imaging element according to claim 16, wherein said transfer switch is an enhancement type transistor.

18. (Currently Amended) A solid state imaging element according to claim 16, wherein said amplifying element amplifier is an enhancement type transistor.

19. (Currently Amended) A solid state imaging element comprising:
a pixel, which has a photoelectric transfer element, a transfer switch for

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transferring charge stored in said photoelectric transfer element, a charge store part for storing charge transferred by said transfer switch, a reset switch for resetting said charge store part, and an amplifying element for outputting a signal in accordance with a the potential of said charge stored in said charge store part to vertical signal lines;

wherein negative voltage is applied to a the gate of said reset switch, and further wherein wherein said reset switch is a depletion type transistor.